
2SD2592L, 2SD2592S

Silicon NPN Triple Diffused
Low Frequency Amplifier

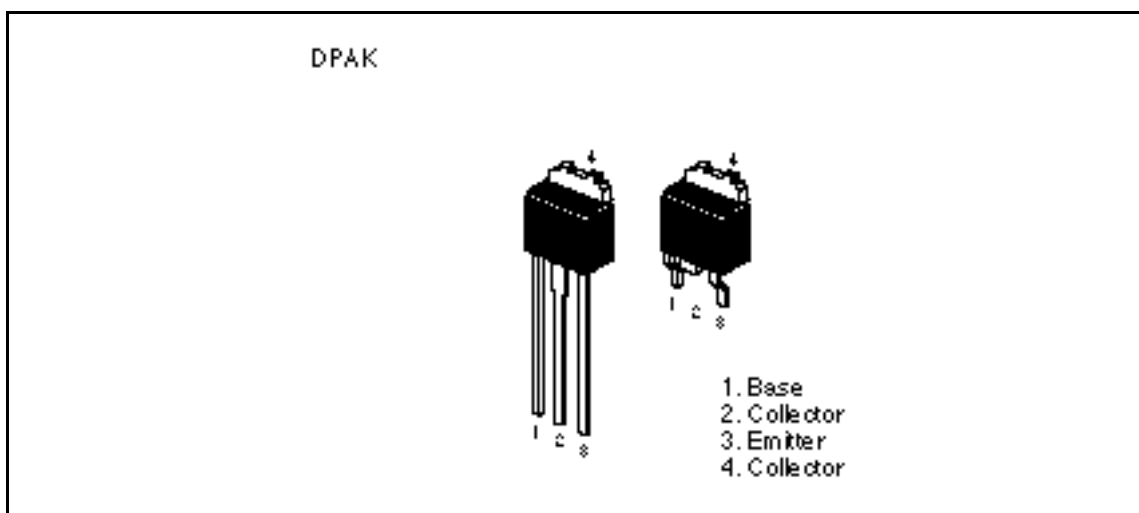
HITACHI

1st. Edition
December 1997
Target Specification

Features

Σ High voltage : $V_{(BR)CEO} = 300V$ min.

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to Base voltage	V_{CBO}	300	V
Collector to Emitter voltage	V_{CEO}	300	V
Emitter to Base voltage	V_{EBO}	5	V
Collector current	I_C	0.15	A
Collector peak current	$I_{C(peak)}$	0.6	A
Collector power dissipation	P_C ^{Note1}	10	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

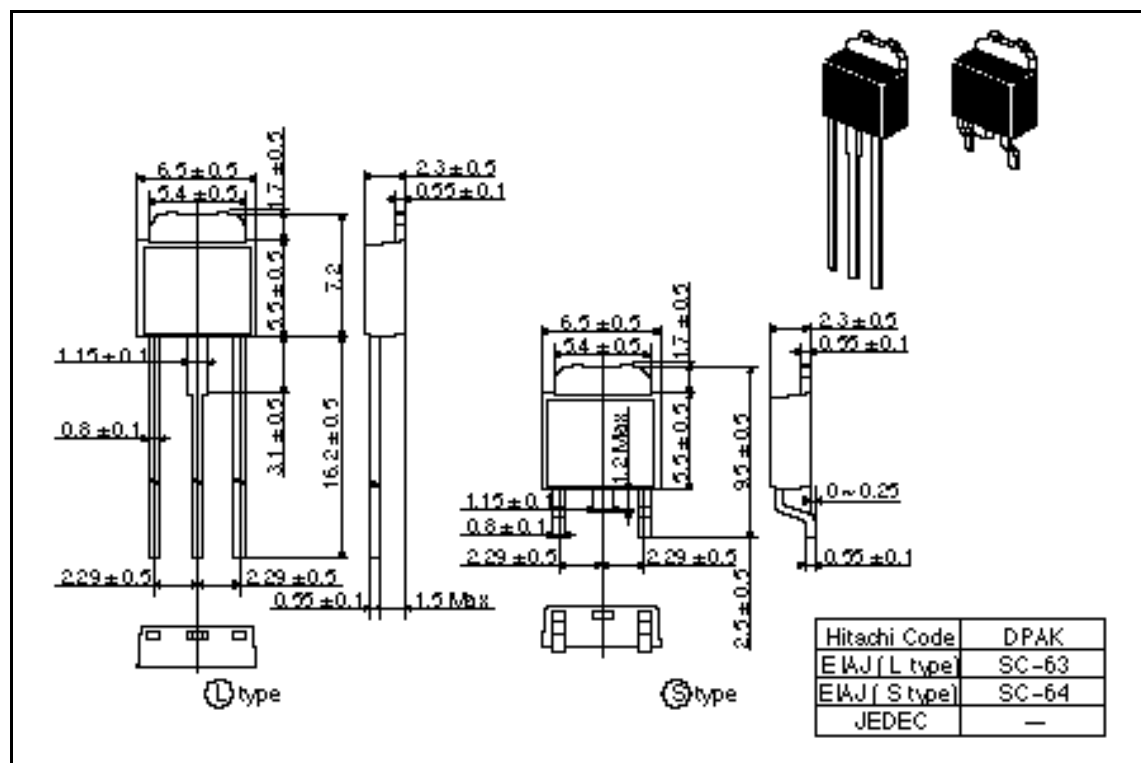
Note: 1. Value at $T_c = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	—	—	V	$I_C = 1\text{mA}$, $R_{BE} = \bullet$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10\text{mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	mA	$V_{CB} = 300\text{V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	10	mA	$V_{EB} = 4\text{V}$, $I_C = 0$
DC current transfer ratio	h_{FE1}	60	—	200		$V_{CE} = 1.5\text{V}$, $I_C = 20\text{mA}$
DC current transfer ratio	h_{FE2}	60	—	—		$V_{CE} = 5\text{V}$, $I_C = 100\text{mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0		$I_C = 100\text{mA}$, $I_B = 5\text{mA}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5		$I_C = 100\text{mA}$, $I_B = 5\text{mA}$
Gain bandwidth product	f_T	—	16	—	MHz	$V_{CE} = 1.5\text{A}$, $I_C = 20\text{mA}$

Package Dimensions

Unit: mm



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